

# GCS InGaAs Monitor PIN PD

P/N: Do213\_SQ260um\_P2



\* Interim part number

### PRELIMINARY DATASHEET



### Introduction

This product is a front side illuminated InGaAs monitor PIN photodiode chip that features a planar structure with anode on front side and cathode on backside. The product has a large  $264 \times 264 \mu m$  square window which has an equivalent detection area to a traditional  $300 \mu m$ -diameter round window MPD. The product is designed primary to be integrated with a FP or DFB laser in a hermetic TO package, for monitoring the optical power output emitted from the back facet of the edge emitting laser, in the wavelength region from 980nm to 1620nm.

## **Key Features**

- A 300μm-diameter equivalent square optical detection window optimized for monitoring FP or DFB lasers
- Planar structure on n+ InP substrate with top anode contact
- Excellent responsivity and low operating bias voltage
- -40C to 85C operation range
- Deliverable in GCS Known Good Die<sup>TM</sup> with 100% testing and inspection
- RoHS compliant

# **Applications**

Back facet laser power monitoring

### SPECIFICATIONS (T=25C°)

	Conditions	Min.	Typical	Max.	Unit	Notes
Responsivity <sub>1</sub>	1310nm	0.8	0.9	-	A/W	
Responsivity2	1550nm	0.9	0.95	-	A/W	
Capacitance	-5 V	-	4.4	5	pF	
Forward Voltage	1mA	-	0.53	0.57	V	
Breakdown	1μΑ	20	-	-	V	
Dark current	-5V	-	0.5	1	nA	
Bandwidth		-	0.5	-	GHz	

### **Absolute Maximum Rating**

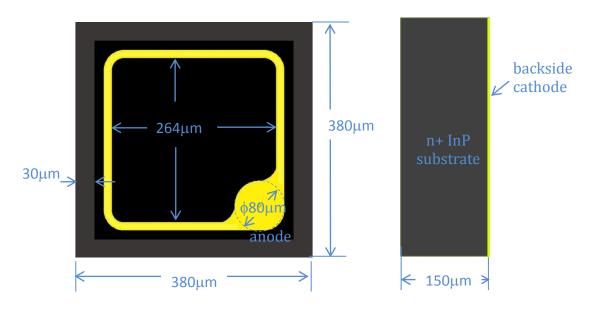
Parameter	Rating			
Reverse Voltage	-20V			
Reverse Current	-10mA			
Forward Current	10mA			
Optical Power Input	10mW			
Operating Temperature	-40C to 85C			
Storage Temperature	-40C to 125C			
Soldering Temperature	320C / 5 sec			



Made in USA

### **Dimensions**

	Conditions	Min.	Typical	Max.	Unit	Notes
Detection Window			264x264		μm	
Bonding pad diameter			80		μm	for p-pad
Metal height of bond pads			1.6	-	μm	Au metal
Die height		140	150	160	μm	
Die width		370	380	390	μm	
Die length		370	380	390	μm	



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Attention: InP brittle material and electrostatic sensitive device, observe precaution for handling.

### **Contact Information**

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About GCS: GCS has a long history manufacturing and shipping both GaAs and InGaAs based photo diodes since 2000. Our state of art manufacturing facility is located in Torrance, California, and has about 10,000 square feet of fab space with a capability of about 1200 4-inch wafers per month and expandable to 2000 wafers per month. GCS as a world-class semiconductor device manufacturer has been delivering a total of over 30 million photo diodes with various date rates and applications used for optical communications, which have been deployed in field by top tier optical transceiver companies worldwide.